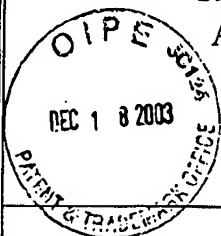


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U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code(s) (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		US			
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FOREIGN PATENT DOCUMENTS

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OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
BK		C.F. Lin et al., "Improved Contact Performance of GaN Film Using Si Diffusion", 2000 American Institute of Physics, Applied Physics Letters, Vol. 76, No. 14, pp. 1878-1880, April 3, 2000
BK		Hiroyuki MASATO et al., "Novel High Drain Breakdown Voltage AlGaIn/GaN HFETs Using Selective Thermal Oxidation Process", IEEE, IEDM 16.2.1-16.2.4, pp. 377-380, 2000

EXAMINER

Bv. Korman

DATE CONSIDERED

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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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